

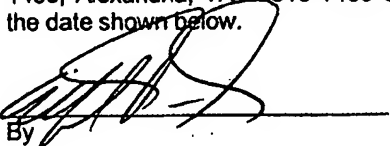


Docket No.: P2001,0273 D

IFW

CERTIFICATION OF MAILING OR TRANSMISSION

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By

December 5, 2006

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Matthias Goldbach et al. Confirmation No.: 9490
Applic. No. : 10/780,075
Docket No. : P2001,0273 D
Filed : February 17, 2004
Title : Stress-Reduced Layer System
Examiner : Hoai Pham Group Art Unit: 2814

OK to enter
HP
12/26/06

Hon. Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR § 1.97(d)

Sir:

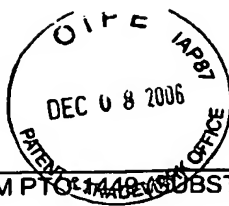
In accordance with 37 CFR 1.98, the following patents and/or publications are cited herewith:

United States Patent Application Publication US 2002/0171099 A1 (Sato et al.), dated November 21, 2002;

Japanese Patent JP 2000-269462 (Sato et al.), dated September 29, 2000, and English abstract thereof;

German Office Action dated September 14, 2006.

In accordance with 37 CFR § 1.97(e) the undersigned herewith states that each item of information contained in the above information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.



FORM PTO-1442 (REV. 10/01) (SUBSTITUTE)				Attorney Docket No.: P2001,0273 D		Applic. No. 10/780,075	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				Applicant Matthias Goldbach et al.			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Filing Date February 17, 2004		Group Art Unit 2814	
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
HP	A	2002/0171099 A1	11/2002	Sato et al.			
	B	5,913,125	06/1999	Brouillette et al.			
	C	5,905,279	05/1999	Nitayama et al.			
	D	6,180,480 B1	01/2001	Economikos et al.			
	E	5,866,452	02/1999	Willer et al.			
HP	F	6,265,741	07/2001	Schrems			
	G						
	H						
	I						
FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
HP	J	2000-269462	09/2000	Japan			
HP	K	44 28 195 C1	04/1995	Germany			
	L						
	M						
	N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
HP	O	K. Yamada et al.: "A Deep- Trenched Capacitor Technology For 4 Mega Bit Dynamic RAM", Proceedings of International Electronic Devices and Materials, IEDM 85, 1985, pp.702-705					
	P						
EXAMINER /Hoai Pham/				DATE CONSIDERED 12/26/2006			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							